


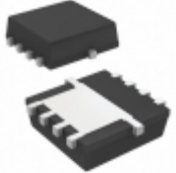

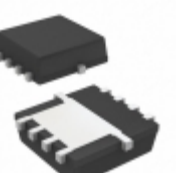



	<p>SI7703EDN-T1-E3</p>
	<p>Hersteller-Teilenummer: SI7703EDN-T1-E3</p> <p>Hersteller / Marke: Vishay / Siliconix</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 4.3A 1212-8</p> <p>Datenblätter:  SI7703EDN-T1-E3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 54740 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI7703EDN-T1-E3
Hersteller	Vishay / Siliconix
Beschreibung	MOSFET P-CH 20V 4.3A 1212-8
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	54740 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® 1212-8
Supplier Device-Gehäuse	PowerPAK® 1212-8
Verlustleistung (max)	1.3W (Ta)
Typ FET	P-Channel
FET-Merkmal	Schottky Diode (Isolated)
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.3A (Ta)
Rds On (Max) @ Id, Vgs	48 mOhm @ 6.3A, 4.5V
VGS (th) (Max) @ Id	1V @ 800µA
Gate Charge (Qg) (Max) @ Vgs	18nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Tape & Reel (TR)













SI7703EDN-T1-E3 ist neu im Original. Suche SI7703EDN-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7703EDN-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7703EDN-T1-E3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI7686DP-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 30V 35A PPAK SO-8</p>	 <p>SI7705DN SILICONX SI7705DN SILICONX</p>	 <p>SI7703EDN-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 4.3A 1212-8</p>	 <p>SI7686DP-T1-GE3 Vishay / Siliconix MOSFET N-CH 30V 35A PPAK SO-8</p>
 <p>SI7703EDN-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 20V 4.3A 1212-8 PPAK</p>	 <p>SI7703EDN-T1-E3 SILICONE SI7703EDN-T1-E3 SILICONE</p>	 <p>SI7703EDN-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 4.3A 1212-8 PPAK</p>	 <p>SI7703EDN-T1 VISHAY SI7703EDN-T1 VISHAY</p>

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|  SI7661CSA+ |  SI7668ADP-T1-E3 |  SI7668ADP-T1-E3 |  SI7668ADP-T1-GE3 |  SI7668ADP-T1-GE3 |
|  SI7674DP |  SI7674DP-T1-GE3 |  SI7674DP-T1-GE3 |  SI7682DP |  SI7682DP-T1-E3 |
|  SI7682DP-T1-E3 |  SI7682DP-T1-GE3 |  SI7682DP-T1-GE3 |  SI7682DY-T1-GE3 |  SI7684DP-T1-GE3 |
|  SI7686DP |  SI7686DP-T1 |  SI7686DP-T1-E3 |  SI7686DP-T1-E3 |  SI7686DP-T1-GE3 |
|  SI7686DP-T1-GE3 |  SI7703DN |  SI7703EDN |  SI7703EDN-T1 |  SI7703EDN-T1-E3 |
|  SI7703EDN-T1-GE3 |  SI7703EDN-T1-GE3 |  SI7703EDN-T1-E3 |  SI7705DN |  SI7705DN-T1 |
|  SI7705DN-T1-E3 |  SI7716ADN |  SI7716ADN-T1-E3 |  SI7716ADN-T1-GE3 |  SI7716ADN-T1-GE3 |
|  SI7716ADN-T1-GE3 |  SI7716DN-T1-GE3 |  SI7720DN-T1-E3 |  SI7720DN-T1-GE3 |  SI7720DN-T1-GE3 |
|  SI7726DN |  SI7726DN-T1-E3 |  SI7726DN-T1-GE3 |  SI7726DN-T1-GE3 |  SI7732DP-T1-GE3 |
|  SI7738DP |  SI7738DP-T1-3 |  SI7738DP-T1-E3 |  SI7738DP-T1-E3 |  SI7738DP-T1-GE3 |

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